



National Semiconductor

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## MM54HC05/MM74HC05 Hex Inverter (Open Drain)

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#### General Description

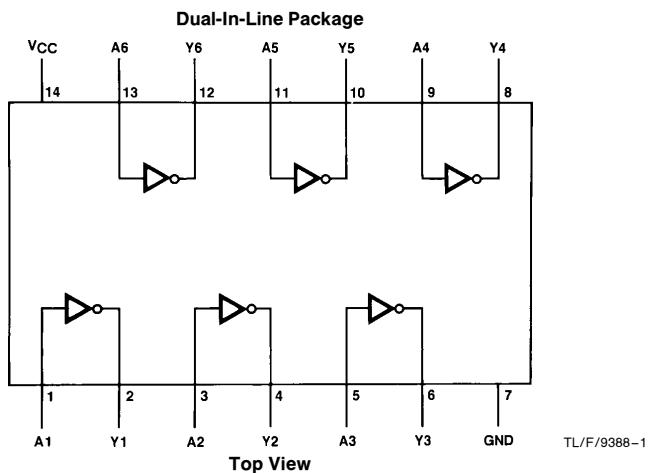
The MM54HC05/MM74HC05 are logic functions fabricated by using advanced silicon-gate CMOS technology, which provides the inherent benefits of CMOS—low quiescent power and wide power supply range. These devices are also functionally and pin-out compatible with standard DM54LS/DM74LS logic families. The MM54HC05/MM74HC05 open drain Hex Inverter requires the addition of an external resistor to perform a wire-NOR function.

All inputs are protected from static discharge damage by internal diodes to V<sub>CC</sub> and ground.

#### Features

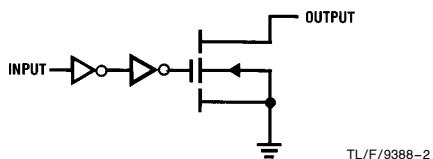
- Open drain for wire-NOR function
- Fanout of 10 LS-TTL loads
- Typical propagation delays:
  - t<sub>PZL</sub> (with 1 kΩ resistor) 8 ns
  - t<sub>PLZ</sub> (with 1 kΩ resistor) 13 ns
- Low input current: 1 μA maximum

#### Connection Diagram

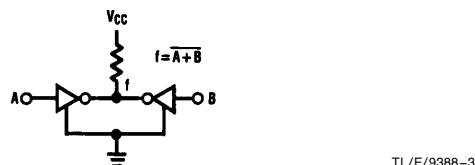


Order Number MM54HC05 or MM74HC05

#### Logic Diagram



#### Typical Application



Note: Can be extended to more than 2 inputs.

## Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage ( $V_{CC}$ )	$-0.5V$ to $+7.0V$
DC Input Voltage ( $V_{IN}$ )	$-1.5V$ to $V_{CC} + 1.5V$
DC Output Voltage ( $V_{OUT}$ )	$-0.5V$ to $V_{CC} + 0.5V$
Clamp Diode Current ( $I_{IK}, I_{OK}$ )	$\pm 20\text{ mA}$
DC Output Current, per pin ( $I_{OUT}$ )	$\pm 25\text{ mA}$
DC $V_{CC}$ or GND Current, per pin ( $I_{CC}$ )	$\pm 50\text{ mA}$
Storage Temperature Range ( $T_{STG}$ )	$-65^{\circ}\text{C}$ to $+150^{\circ}\text{C}$
Power Dissipation ( $P_D$ ) (Note 3) S.O. Package only	600 mW 500 mW
Lead Temperature ( $T_L$ ) (Soldering 10 seconds)	260°C

## Operating Conditions

	Min	Max	Units
Supply Voltage ( $V_{CC}$ )	2	6	V
DC Input or Output Voltage ( $V_{IN}, V_{OUT}$ )	0	$V_{CC}$	V
Operating Temp. Range ( $T_A$ ) MM74HC	$-40$	$+85$	°C
MM54HC	$-55$	$+125$	°C
Input Rise or Fall Times ( $t_r, t_f$ )	$V_{CC} = 2.0V$		
	$1000\text{ ns}$		
	$V_{CC} = 4.5V$		
	$500\text{ ns}$		
	$V_{CC} = 6.0V$		
	$400\text{ ns}$		

## DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	$V_{CC}$	$T_A = 25^{\circ}\text{C}$		$74\text{HC}$	$54\text{HC}$	Units
				Typ		$T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$	$T_A = -55^{\circ}\text{C}$ to $+125^{\circ}\text{C}$	
$V_{IH}$	Minimum High Level Input Voltage		2.0V 4.5V 6.0V	1.5 3.15 4.2		1.5 3.15 4.2	1.5 3.15 4.2	V
$V_{IL}$	Maximum Low Level Input Voltage**		2.0V 4.5V 6.0V	0.5 1.35 1.8		0.5 1.35 1.8	0.5 1.35 1.8	V
$V_{OL}$	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ $ I_{OUT}  \leq 20\text{ }\mu\text{A}$ $R_L = \infty$	2.0V 4.5V 6.0V	0 0 0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ $ I_{OUT}  \leq 4.0\text{ mA}$ $ I_{OUT}  \leq 5.2\text{ mA}$	4.5V 6.0V	0.2 0.2	0.26 0.26	0.33 0.33	0.4 0.4	V
$I_{LKG}$	Maximum High Level Output Leakage Current	$V_{IN} = V_{IH}$ or $V_{IL}$ $V_{OUT} = V_{CC}$	6.0V		0.5	5	10	$\mu\text{A}$
$I_{IN}$	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		$\pm 0.1$	$\pm 1.0$	$\pm 1.0$	$\mu\text{A}$
$I_{CC}$	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0\text{ }\mu\text{A}$	6.0V		2.0	20	40	$\mu\text{A}$

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package:  $-12\text{ mW}/^{\circ}\text{C}$  from  $65^{\circ}\text{C}$  to  $85^{\circ}\text{C}$ ; ceramic "J" package:  $-12\text{ mW}/^{\circ}\text{C}$  from  $100^{\circ}\text{C}$  to  $125^{\circ}\text{C}$ .

Note 4: For a power supply of  $5V \pm 10\%$  the worst case output voltages ( $V_{OH}$  and  $V_{OL}$ ) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case  $V_{IH}$  and  $V_{IL}$  occur at  $V_{CC} = 5.5V$  and 4.5V respectively. (The  $V_{IH}$  value at 5.5V is 3.85V.) The worst case leakage current ( $I_{IN}$ ,  $I_{CC}$ , and  $I_{OZ}$ ) occur for CMOS at the higher voltage and so the 6.0V values should be used.

\*\* $V_{IL}$  limits are currently tested at 20% of  $V_{CC}$ . The above  $V_{IL}$  specification (30% of  $V_{CC}$ ) will be implemented no later than Q1, CY'89.

### AC Electrical Characteristics $V_{CC} = 5V$ , $T_A = 25^\circ C$ , $C_L = 15 \text{ pF}$ , $t_r = t_f = 6 \text{ ns}$

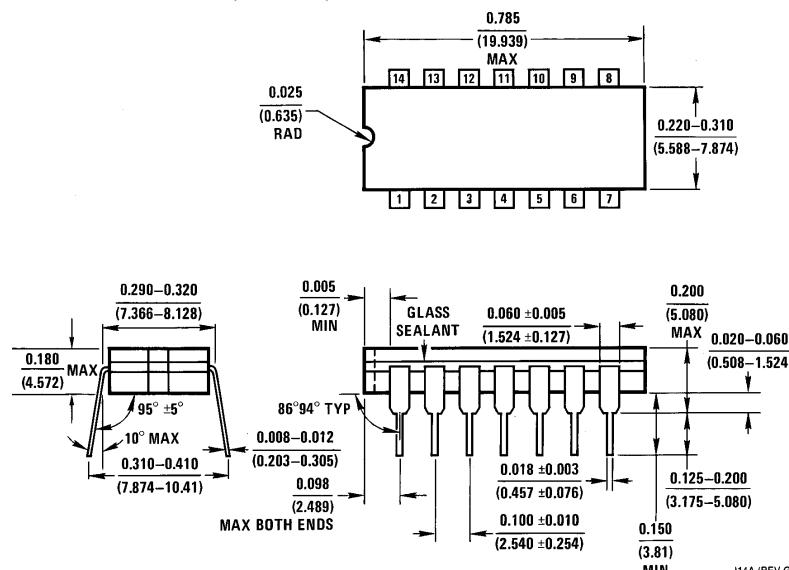
Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
$t_{PZL}, t_{PLZ}$	Maximum Propagation Delay	$R_L = 1 \text{ k}\Omega$	8		ns

### AC Electrical Characteristics $V_{CC} = 2.0V \text{ to } 6.0V$ , $C_L = 50 \text{ pF}$ , $t_r = t_f = 6 \text{ ns}$ unless otherwise specified

Symbol	Parameter	Conditions	$V_{CC}$	74HC			54HC	Units
				Typ	Guaranteed Limits			
$t_{PZL}$	Maximum Propagation Delay	$R_L = 1 \text{ k}\Omega$	2.0V	30	75	95	110	ns
			4.5V	8	15	19	22	
			6.0V	7	13	16	19	
$t_{PLZ}$	Maximum Propagation Delay	$R_L = 1 \text{ k}\Omega$	2.0V	30	90	115	135	ns
			4.5V	13	18	23	27	
			6.0V	12	15	20	23	
$t_{THL}$	Maximum Output Fall Time		2.0V	30	75	95	110	ns
			4.5V	8	15	19	22	
			6.0V	7	13	16	19	
$C_{PD}$	Power Dissipation Capacitance (Note 5)	(per gate)		8				pF
$C_{IN}$	Maximum Input Capacitance			5	10	10	10	pF

Note 5:  $C_{PD}$  determines the no load dynamic power consumption,  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ , and the no load dynamic current consumption,  $I_S = C_{PD} V_{CC} f + I_{CC}$ . The power dissipated by  $R_L$  is not included.

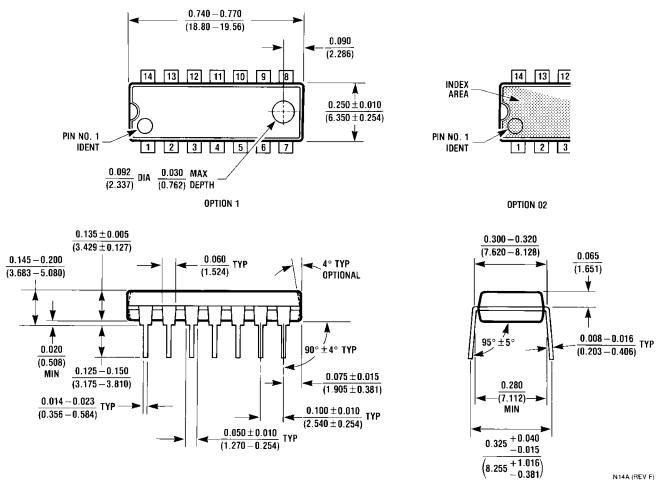
### Physical Dimensions inches (millimeters)



Order Number MM54HC05J or MM74HC05J  
NS Package Number J14A

# MM54HC05/MM74HC05 Hex Inverter (Open Drain)

## Physical Dimensions inches (millimeters) (Continued)



**Order Number MM74HC05N  
NS Package Number N14A**

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